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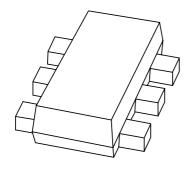
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PMEG2010EVLow V_F MEGA Schottky barrier diode

Product data sheet Supersedes data of 2002 Jun 24 2003 Aug 20



Low V_F MEGA Schottky barrier diode

PMEG2010EV

FEATURES

Forward current: 1 AReverse voltage: 20 V

Very low forward voltage

Ultra small SMD package

• Flat leads: excellent coplanarity and improved thermal behaviour.

APPLICATIONS

• Low voltage rectification

• High efficiency DC/DC conversion

• Switch mode power supply

• Inverse polarity protection

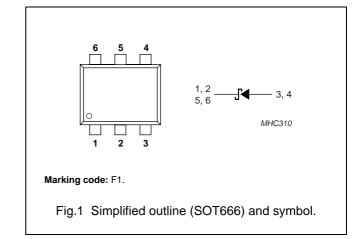
• Low power consumption applications.

DESCRIPTION

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection in a SOT666 ultra small SMD plastic package.

PINNING

| PIN | DESCRIPTION | |
|-----|-------------|--|
| 1 | cathode | |
| 2 | cathode | |
| 3 | anode | |
| 4 | anode | |
| 5 | cathode | |
| 6 | cathode | |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134)

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------------|---|------|------|------|
| V _R | continuous reverse voltage | | _ | 20 | V |
| I _F | continuous forward current | | _ | 1 | Α |
| I _{FSM} | non-repetitive peak forward current | t = 8.3 ms half sinewave; JEDEC method; note 1 | _ | 8 | А |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| Tj | junction temperature | | _ | 125 | °C |
| T _{amb} | operating ambient temperature | | -65 | +125 | °C |

Note

1. Only valid if pins 3 and 4 are connected in parallel.

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THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 405 | K/W |
| | | note 2 | 215 | K/W |

Notes

- 1. Refer to SOT666 standard mounting conditions.
- 2. Mounted on printed circuit-board, 1 cm² copper area.

Soldering

The only recommended soldering method is reflow soldering.

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|----------------|----------------------------|---|------|------|------|
| V _F | continuous forward voltage | I _F = 10 mA | 240 | 270 | mV |
| | | I _F = 100 mA | 300 | 350 | mV |
| | | I _F = 1000 mA; note 1; see Fig.2 | 480 | 550 | mV |
| I _R | reverse current | V _R = 5 V; note 2 | 5 | 10 | μΑ |
| | | V _R = 8 V; note 2 | 7 | 20 | μΑ |
| | | V _R = 15 V; note 2; see Fig.3 | 10 | 50 | μΑ |
| C _d | diode capacitance | V _R = 5 V; f = 1 MHz; see Fig.4 | 19 | 25 | pF |

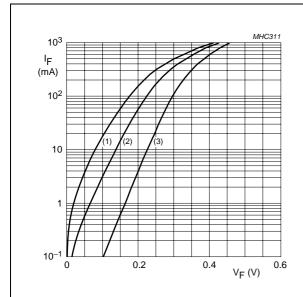
Notes

- 1. Only valid if pins 1, 2, 5 and 6 are soldered on a 1 cm² copper solder land.
- 2. Pulse test: t_p = 300 μ s; δ = 0.02.

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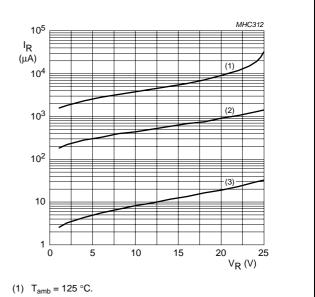
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GRAPHICAL DATA



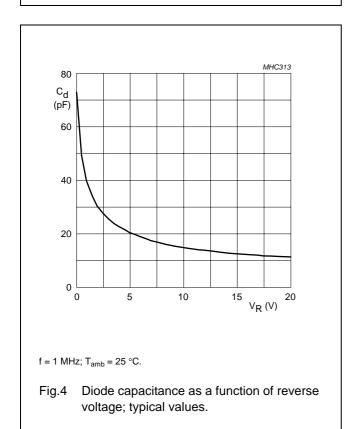
- (1) $T_{amb} = 125 \, ^{\circ}C$.
- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (2) $T_{amb} = 85 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



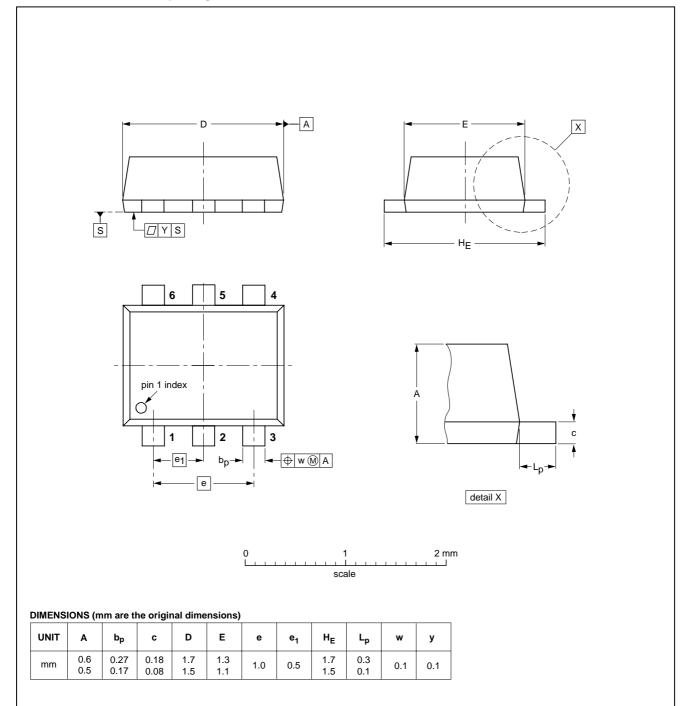
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PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



| OUTLINE | REFERENCES EUROPEAN ISSU | | | ISSUE DATE | |
|---------|--------------------------|-------|------|-----------------------|----------------------------------|
| VERSION | IEC | JEDEC | EIAJ | PROJECTION 1550E DATE | |
| SOT666 | | | | | -01-01-04 01-08-27 |

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DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|-----------------------------------|----------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- The product status of device(s) described in this document may have changed since this document was published
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NXP Semiconductors

Customer notification

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Contact information

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